BC546/BC547/BC548

TO-92 Plastic-Encapsulate Transistors

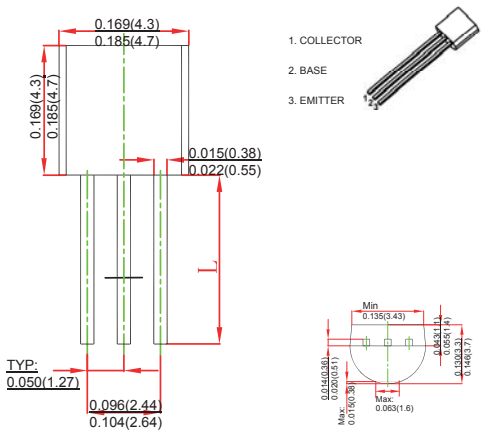
FEATURES

- High Voltage
- Complement to BC556,BC557,BC558
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage	BC546	80	V
		BC547	50	
		BC548	30	
V_{CEO}	Collector-Emitter Voltage	BC546	65	V
		BC547	45	
		BC548	30	
V_{EBO}	Emitter-Base Voltage	BC546	6	V
		BC547	6	V
		BC548	5	V
I_C	Collector Current-Continuous		0.1	A
P_C	Collector Power Dissipation		625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient		200	℃/W
T_j	Junction Temperature		150	℃
T_{stg}	Storage Temperature		-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BC546	$V_{(BR)CBO}$	I_C= 0.1mA,I_E=0	80			V
	BC547			50			
	BC548			30			
Collector-emitter breakdown voltage	BC546	$V_{(BR)CEO}$	I_C=1mA,I_B=0	65			V
	BC547			45			
	BC548			30			
Emitter-base breakdown voltage	BC546	$V_{(BR)EBO}$	I_E=10μA,I_C=0	6			V
	BC547			6			
	BC548			5			
Collector cut-off current	BC546	I_{CBO}	V_{CB}=70V,I_E=0			0.1	μA
	BC547		V_{CB}=50V,I_E=0			0.1	μA
	BC548		V_{CB}=30V,I_E=0			0.1	μA
Collector cut-off current	BC546	I_{CEO}	V_{CE}=60V,I_B=0			0.1	μA
	BC547		V_{CE}=45V,I_B=0			0.1	μA
	BC548		V_{CE}=30V,I_B=0			0.1	μA
Emitter cut-off current		I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain		h_{FE}*	V_{CE}=5V, I_C=2mA	110		800	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=100mA,I_B=5mA			0.3	V
Base-emitter saturation voltage		$V_{BE(sat)}$	I_C=100mA,I_B=5mA			1.1	V
Base-emitter voltage		V_{BE}	V_{CE}=5V, I_C=2mA	0.58		0.7	V
			V_{CE}=5V, I_C=10mA			0.75	V
Collector output capacitance		C_{ob}	V_{CB}=10V,I_E=0, f=1MHz			4.5	pF
Transition frequency		f_T	V_{CE}=5V,I_C=10mA, f=100MHz	150			MH

CLASSIFICATION of h_{FE}

RANK	A	B	C
RANGE	110-220	200-450	420-800